

# P-Channel 30-V (D-S) MOSFET

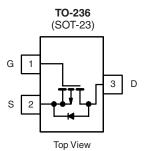
PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A) <sup>b</sup>			
- 30	0.078 at V <sub>GS</sub> = - 10 V	- 3.2			
	0.130 at V <sub>GS</sub> = - 4.5 V	- 2.5			

#### **FEATURES**

- Halogen-free Option Available
- TrenchFET® Power MOSFET







Si2307BDS (L7)\*

\* Marking Code

Ordering Information: Si2307BDS-T1-E3 (Lead (Pb)-free)

Si2307BDS-T1-GE3 (Lead (Pb)-free and Halogen-free)

<b>ABSOLUTE MAXIMUM RATINGS</b> T <sub>A</sub> = 25 °C, unless otherwise noted						
Parameter		Symbol	5 s	Steady State	Unit	
Drain-Source Voltage		$V_{DS}$	- 30			
Gate-Source Voltage		V <sub>GS</sub>	± 20		V	
Ocationary Durin Compat (T., 450 cO)b	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	- 3.2	- 2.5		
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>b</sup>	T <sub>A</sub> = 70 °C		- 2.6	- 2.0		
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	- 12		А	
Continuous Source Current (Diode Conduction) <sup>b</sup>		I <sub>S</sub>	- 1.25	- 0.75		
Decree Director than h	T <sub>A</sub> = 25 °C	- P <sub>D</sub>	1.25	0.75	W	
Power Dissipation <sup>b</sup>	T <sub>A</sub> = 70 °C		0.8	0.48	] vv	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient <sup>b</sup>	- R <sub>thJA</sub>	80	100	°C/W		
Maximum Junction-to-Ambient <sup>c</sup>	' 'thJA	130	166	C/VV		

#### Notes:

- a. Pulse width limited by maximum junction temperature.
- b. Surface Mounted on FR4 board,  $t \le 5$  s.
- c. Surface Mounted on FR4 board.

For SPICE model information via the Worldwide Web: http://www.vishay.com/www/product/spice.htm

# Vishay Siliconix



<b>SPECIFICATIONS</b> T <sub>J</sub> = 25 °C, unless otherwise noted							
			Limits				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_D = -10 \mu\text{A}$	- 30			V	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = -250 \mu A$	- 1.0		- 3.0	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current		V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = 0 V			- 1	μΑ	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			- 10		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le$ - 10 V, $V_{GS} =$ - 10 V	- 6			Α	
5	В	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 3.2 A		0.063	0.078	Ω	
Drain-Source On-Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, I_D = -2.5 \text{ A}$		0.105	0.130		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 3.2 A		5.0		S	
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> = - 0.75 A, V <sub>GS</sub> = 0 V		- 0.85	- 1.2	V	
Dynamic <sup>b</sup>	'				•		
Total Gate Charge	Qg	V 45.V.V 40.V		9.0	15		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}$ $I_{D} \cong -1.7 \text{ A}$		1.4		nC	
Gate-Drain Charge	$Q_{gd}$	ID=-1.7 A		2.4			
Gate Resistance	$R_g$	f = 1.0 MHz		8.0		Ω	
Input Capacitance	C <sub>iss</sub>			380			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		100		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			75			
Switching <sup>c</sup>							
Turn On The s	t <sub>d(on)</sub>	$V_{DD} = -15 \text{ V}, R_L = 15 \Omega$ $V_{DD} = -10 \text{ A}, V_{GEN} = -4.5 \text{ V}$		9	20	- ns	
Turn-On Time				12	20		
Turn-Off Time	t <sub>d(off)</sub>	$R_{\rm q} = 6 \Omega$		25	40		
Turn-Oil Time	t <sub>f</sub>	· ·y		14	21		

#### Notes:

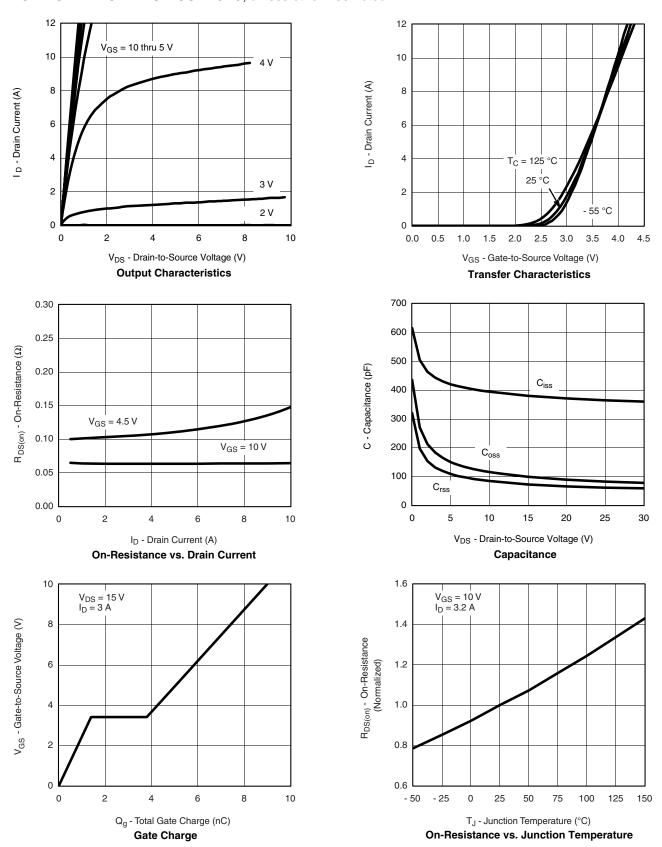
- a. Pulse test: pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



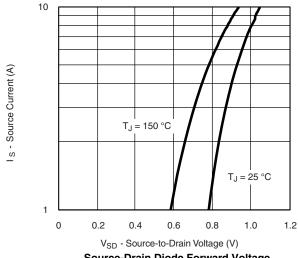


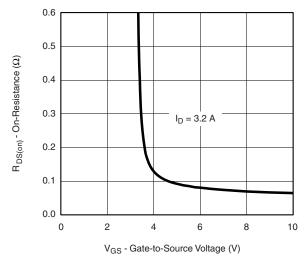
### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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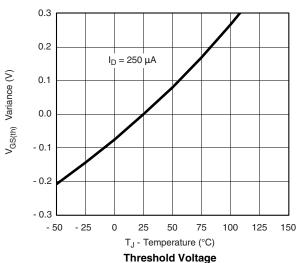
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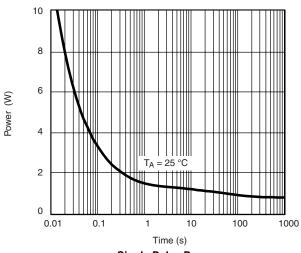




### Source-Drain Diode Forward Voltage

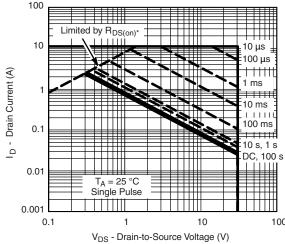








**Single Pulse Power** 

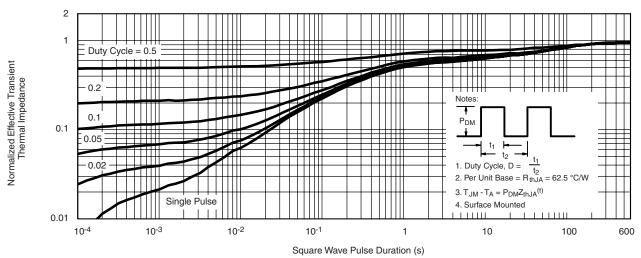


\*  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified Square Wave Pulse Duration (s)

Safe Operating Area, Junction-to-Case



#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient

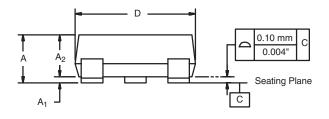
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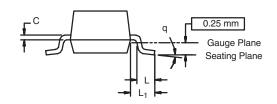
Document Number: 72699 S-80427-Rev. C, 03-Mar-08

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## SOT-23 (TO-236): 3-LEAD







Dim	MILLIN	IETERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A <sub>1</sub>	0.01	0.10	0.0004	0.004	
A <sub>2</sub>	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E <sub>1</sub>	1.20	1.40	0.047	0.055	
е	0.95	BSC	0.0374 Ref		
e <sub>1</sub>	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L <sub>1</sub>	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
ECN: S-03946-Rev. K. 09-	Jul-01				

DWG: 5479

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#### **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE

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